

Notice of References Cited	Application/Control No. 10/821,957	Applicant(s)/Patent Under Reexamination SUZUKI, TAKAYUKI	
	Examiner Elizabeth Ivey	Art Unit 1775	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	"High Quality Growth of AlN Epitaxial Layer by Plasma-Assisted Molecular-Beam Epitaxy" by Kulandaivel Jeganathan, Toshio Kitamura, Mitsuaki Shimizu and Hajime Okumura; Japan Journal of Applied Physics; Vol. 41, 2002; pp. L28-L30 Part 2, No. 1A/B, 15 January 2002.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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